

Crystal Oscillator Module ICs

OVERVIEW

The CF5014 series are fundamental frequency crystal oscillator ICs. They are available for frequencies up to 60MHz. The chip layout is optimized, resulting in a large reduction in chip size, when compared to existing devices.

FEATURES

- 2.7 to 5.5V operating supply voltage range
- Up to 60MHz oscillation frequency range
- -40 to 85°C operating temperature range
- Oscillation capacitors built-in
 - $C_G = 18pF, C_D = 18pF$
- Inverter amplifier feedback resistor built-in
- Standby function
 - High impedance in standby mode, oscillator stops
- Low standby current
 - Power-saving pull-up resistor built-in
- f_O, f_O/2, f_O/4, f_O/8, or f_O/16 output frequency, determined by internal connection
- CMOS output duty level (1/2VDD)
- Molybdenum-gate CMOS process
- Chip form (CF5014AL×)

SERIES CONFIGURATION

	Recommended	Recommended operating frequency range ¹ [MHz]			pacitance		Standby				
Version	V _{DD} = 2.7	7 to 3.6V	V _{DD} = 4.5 to 5.5V	[pF]		[pF]		[pF]		[pF] Output frequency	
	C _L = 15pF	C _L = 30pF	C _L = 30pF	C _G	C _D						
CF5014AL1						f _O	Yes				
CF5014AL2						f _O /2	Yes				
CF5014AL3	4 to 60	4 to 40	4 to 60	18	18	f _O /4	Yes				
CF5014AL4							f _O /8	Yes			
CF5014AL5						f _O /16	Yes				

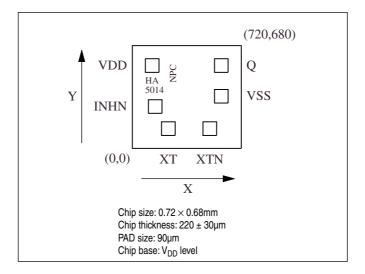
The recommended operating frequency is a yardstick value derived from the crystal used for NPC characteristics authentication. However, the
oscillator frequency band is not guaranteed. Specifically, the characteristics can vary greatly due to crystal characteristics and mounting conditions, so the oscillation characteristics of components must be carefully evaluated.

ORDERING INFORMATION

Device	Package
CF5014AL×-2	Chip form

PAD LAYOUT

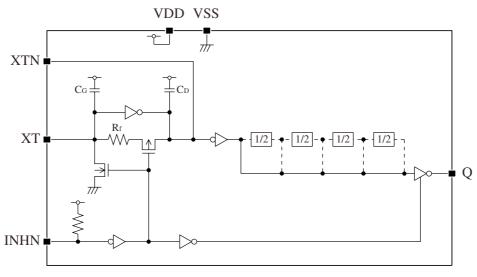
(Unit: µm)



PIN DESCRIPTION and PAD DIMENSIONS

Name	1/0	Description			sions [µm]
Name	Name #0 Description		Х	Υ	
INHN	I		tput state control input. High impedance when LOW (oscillator stops). wer-saving pull-up resistor built-in.		277
XT	I	Amplifier input	Crystal connection pins.	238	131
XTN	0	Amplifier output	Crystal is connected between XT and XTN.	512	131
VSS	-	Ground		588	345
Q	0	Output. Output frequence	Output. Output frequency (f _O , f _O /2, f _O /4, f _O /8, f _O /16) determined by internal connection		548
VDD	-	Supply voltage		131	548

BLOCK DIAGRAM



INHN = LOW active

SPECIFICATIONS

Absolute Maximum Ratings

$$V_{SS} = 0V$$

Parameter	Symbol	Condition	Rating	Unit
Supply voltage range	V _{DD}		-0.5 to +7.0	V
Input voltage range	V _{IN}		-0.5 to V _{DD} + 0.5	
Output voltage range	V _{OUT}		-0.5 to V _{DD} + 0.5	
Operating temperature range	T _{opr}		-40 to +85	°C
Storage temperature range	T _{STG}		-65 to +150	°C
Output current	I _{OUT}		12	mA

Recommended Operating Conditions

3V operation

$$V_{SS} = 0V$$

Parameter	Symbol	Condition	Rating	Unit
Supply voltage range	V _{DD}		2.7 to 3.6	V
Input voltage range	V _{IN}		V _{SS} to V _{DD}	V
Operating temperature range	T _{OPR}		-40 to +85	°C
Operating frequency range	f	$C_L \le 15pF$	4 to 60	MHz
Operating frequency range	fosc f	$C_L \le 30pF$	4 to 40	MHz

5V operation

$$V_{SS} = 0V$$

Parameter	Symbol	Condition	Rating	Unit
Supply voltage range	V _{DD}		4.5 to 5.5	V
Input voltage range	V _{IN}		V _{SS} to V _{DD}	٧
Operating temperature range	T _{OPR}		-40 to +85	°C
Operating frequency range	fosc	$C_L \le 30pF$	4 to 60	MHz

Electrical Characteristics

3V operation

 $V_{\rm DD}$ = 2.7 to 3.6V, $V_{\rm SS}$ = 0V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Complete	Condition			Rating		
Parameter	Symbol			min	typ	max	Unit
HIGH-level output voltage	V _{OH}	Q: Measurement cct 1, V _{DD} = 2.7V, I _{OH} =	4mA	2.1	2.4	-	٧
LOW-level output voltage	V _{OL}	Q: Measurement cct 1, V _{DD} = 2.7V, I _{OL} =	4mA	-	0.3	0.4	V
HIGH-level input voltage	V _{IH}	INHN		0.7V _{DD}	-	-	٧
LOW-level input voltage	V _{IL}	INHN		-	-	0.3V _{DD}	٧
Output looks as surrent		O. Maggurament act 0 INILIN I OW	$V_{OH} = V_{DD}$	-	-	10	μΑ
Output leakage current	I _Z	Q: Measurement cct 2, INHN = LOW	V _{OL} = V _{SS}	-	-	10	μΑ
	I _{DD}	Measurement cct 3, load cct 1, INHN = open, C _L = 15pF, f = 60MHz CF5014AL2 CF5014AL3 CF5014AL4 CF5014AL5	CF5014AL1	-	6.5	13	mA
			CF5014AL2	-	4	8	mA
Current consumption			CF5014AL3	-	3	6	mA
			CF5014AL4	-	2.5	5	mA
			-	2	4	mA	
Standby current	I _{ST}	Measurement cct 3, INHN = LOW		-	-	5	μΑ
INII INI mulli un vaniataman	R _{UP1}	Management and 4		2	6	18	МΩ
INHN pull-up resistance R _{UP}		Measurement cct 4	30	100	300	kΩ	
Feedback resistance	R _f	Measurement cct 5		100	300	600	kΩ
Duilt in consistence	C _G	Design value A monitor nottors	ar in tootod	15.3	18	20.7	pF
Built-in capacitance	C _D	Design value. A monitor pattern on a wafe	15.3	18	20.7	pF	

CF5014 series

5V operation

 $V_{\rm DD}$ = 4.5 to 5.5V, $V_{\rm SS}$ = 0V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Cumbal	Condition			Rating		Unit
Parameter	Symbol			min	typ	max	Unit
HIGH-level output voltage	V _{OH}	Q: Measurement cct 1, V _{DD} = 4.5V, I _{OH} =	8mA	3.9	4.2	-	٧
LOW-level output voltage	V _{OL}	Q: Measurement cct 1, V _{DD} = 4.5V, I _{OL} =	8mA	-	0.3	0.4	٧
HIGH-level input voltage	V _{IH}	INHN		0.7V _{DD}	-	-	٧
LOW-level input voltage	V _{IL}	INHN		-	-	0.3V _{DD}	٧
Outrat Incline a comment		O. Management and O. INIJIN. J. COM.	$V_{OH} = V_{DD}$	-	-	10	μΑ
Output leakage current I _Z		Q: Measurement cct 2, INHN = LOW	V _{OL} = V _{SS}	-	-	10	μΑ
	I _{DD}	Measurement cct 3, load cct 1, INHN = open, C _L = 30pF, f = 60MHz	CF5014AL1	-	17	34	mA
			CF5014AL2	_	11.5	23	mA
Current consumption			CF5014AL3	-	8.5	17	mA
			CF5014AL4	-	7	14	mA
		CF5014AL5		-	6	12	mA
Standby current	I _{ST}	Measurement cct 3, INHN = LOW		_	-	10	μA
INITIAL CONTRACTOR OF CONTRACT	R _{UP1}	Management		1	3	9	MΩ
INHN pull-up resistance	R _{UP2}	Measurement cct 4		10	50	150	kΩ
Feedback resistance	R _f	Measurement cct 5		100	300	600	kΩ
Duilt in conscitones	C _G	Design value. A monitor pattern on a wafer is tested.		15.3	18	20.7	pF
Built-in capacitance	C _D			15.3	18	20.7	pF

Switching Characteristics

3V operation

 $V_{DD} = 2.7$ to 3.6V, $V_{SS} = 0$ V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Cumbal	Condition	Rating			Unit	
Farameter	Symbol	Condition			typ	max	Ullit
Output rise time	t _{r1}	Measurement cct 3, load cct 1,	C _L = 15pF	-	3	6	no
Output rise time	t _{r2}	0.1V _{DD} to 0.9V _{DD}	C _L = 30pF	-	5	10	ns
Outrast fall for a	t _{f1}	Measurement cct 3, load cct 1,	C _L = 15pF	_	3	6	
Output fall time	t _{f2}	0.9V _{DD} to 0.1V _{DD}	C _L = 30pF	-	5	10	ns
Output duty quala	Duty1	Measurement cct 3, load cct 1,	C _L = 15pF f = 60MHz	45	-	55	%
Output duty cycle ¹	Duty2	V _{DD} = 3.0V, Ta = 25°C	C _L = 30pF f = 40MHz	45	-	55	%
Output disable delay time ²	t _{PLZ}	Measurement cct 6, load cct 1, V _{DD} = 3.0V, Ta = 25°C,		-	-	100	ns
Output enable delay time ²	t _{PZL}	C _L = 15pF	-	-	100	ns	

^{1.} The duty cycle characteristic is checked the sample chips of each production lot.

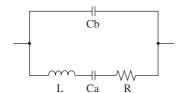
5V operation

 $V_{\rm DD}$ = 4.5 to 5.5V, $V_{\rm SS}$ = 0V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
Parameter	Syllibol	Condition			typ	max	Ullit
Output rise time	t _{r1}	Measurement cct 3, load cct 1,	C _L = 15pF	-	1.8	3.5	ne
Output rise time	t _{r2}	0.1V _{DD} to 0.9V _{DD}	C _L = 30pF	_	3	6	ns
Output fall time	t _{f1}	Measurement cct 3, load cct 1,	C _L = 15pF	-	1.8	3.5	ns
Output fail time	t _{f2}	0.9V _{DD} to 0.1V _{DD}	C _L = 30pF	-	3	6	115
Output duty cycle ¹	Duty1	Measurement cct 3, load cct 1, V _{DD} = 5.0V, Ta = 25°C	C _L = 30pF f = 60MHz	45	-	55	%
Output disable delay time ²	t _{PLZ}	Measurement cct 6, load cct 1, V _{DD} = 5.0V,	-	-	100	ns	
Output enable delay time ²	t _{PZL}	C _L = 15pF		_	_	100	ns

^{1.} The duty cycle characteristic is checked the sample chips of each production lot.

Current consumption and Output waveform with NPC's standard crystal



f [MHz]	R [Ω]	L [mH]	Ca [fF]	Cb [pF]
40	8.23	5.72	2.77	2.20
50	16.12	6.88	1.48	1.15
60*	_	_	-	_

^{*} The 60MHz crystal data is confidential.

^{2.} Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

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FUNCTIONAL DESCRIPTION

Standby Function

When INHN goes LOW, the oscillator stops and the oscillator output on Q becomes high impedance.

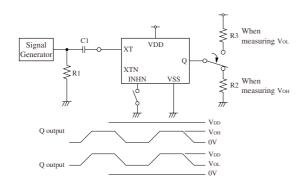
INHN	INHN Q	
HIGH (or open)	HIGH (or open) Any f _O , f _O /2, f _O /4, f _O /8 or f _O /16 output frequency	
LOW	High impedance	Stopped

Power-saving Pull-up Resistor

The INHN pull-up resistance changes in response to the input level (HIGH or LOW). When INHN goes LOW (standby state), the pull-up resistance becomes large to reduce the current consumption during standby.

MEASUREMENT CIRCUITS

Measurement cct 1



2Vp-p, 10MHz sine wave input signal

C1: 0.001µF

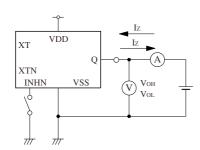
R1: 50Ω

R2: 525Ω (3V operation)

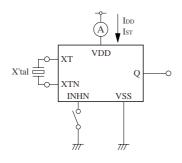
488Ω (5V operation)

R3: 575Ω (3V operation) 512Ω (5V operation)

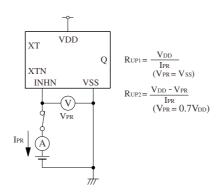
Measurement cct 2



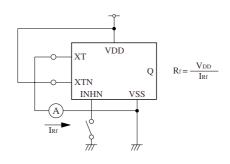
Measurement cct 3



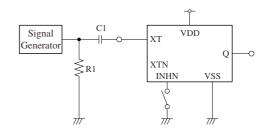
Measurement cct 4



Measurement cct 5



Measurement cct 6

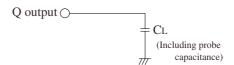


2Vp-p, 10MHz sine wave input signal

C1: 0.001µF

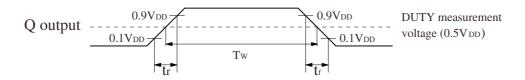
R1: 50Ω

Load cct 1

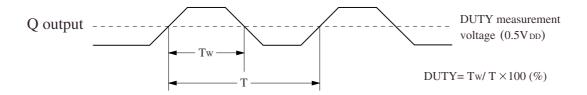


Switching Time Measurement Waveform

Output duty level

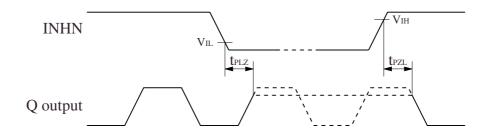


Output duty cycle



Output Enable/Disable Delay

when the device is in standby, the oscillator stops. When standby is released, the oscillator starts and stable oscillator output occurs after a short delay.



INHN input waveform $tr = tf \le 10ns$

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SEIKO NPC CORPORATION

1-9-9, Hatchobori, Chuo-ku, Tokyo 104-0032, Japan Telephone: +81-3-5541-6501 Facsimile: +81-3-5541-6510 http://www.npc.co.jp/ Email: sales@npc.co.jp

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